

The 21st Korean Conference on Semiconductors
제21회 한국반도체학술대회
February 24–26, 2014 / Hanyang University, Seoul, Korea

K. Memory (Design & Process Technology) 분과

[WK3-K] Resistive Memory Devices for Cross-Point Array

Date	Feb. 26, 2014 (Wed.)
Place	Room K / 제1공학관 502호 (# 502, Engineering Building I)

Session Chair: 김수길 박사(SK hynix), 백승재 교수(한경대학교)

- WK3-K-1 15:50-16:05 Excellent Non-Linear I-V Characteristics of Ti/HfO_x ReRAM with Ultrathin TiO_y Tunnel Barrier for Cross Point Memory Application**
저자: Nusrat Tamanna, Saiful Haque Misha, Amit Prakash, Daeseok Lee, Jiyoung Woo, Euijun Cha, Jeonghwan Song, Kibong Moon, and Hyunsang Hwang
소속: Department of Materials Science and Engineering, Pohang University of Science and Technology
- WK3-K-2 16:05-16:20 Characterization of γ -Fe₂O₃ Memristors via Physics-Based Empirical I-V Model**
저자: Yun Hyeok Kim¹, Dae Guen Kim¹, Jae-Deuk Kim², Sung-Jin Choi¹, Dong Myong Kim¹, Tae-Sik Yoon², and Dae Hwan Kim¹
소속: ¹School of Electrical Engineering, Kookmin University, ²Department of Materials Science and Engineering, Myongji University
- WK3-K-3 16:20-16:35 Identification of Controlling Parameters on Self-Compliance Resistive Switching in a Pt/TaO_x/Ta₂O₅/Pt Structure**
저자: Taehyung Park, Seul Ji Song, Jun Yeong Seok, Jung Ho Yoon, Kyung Jean Yoon, Dae Eun Kwon, and Cheol Seong Hwang
소속: Department of Material Science and Engineering, Seoul National University
- WK3-K-4 16:35-16:50 Cu₂O-Based Conductive Bridging Random-Access-Memory**
저자: Ki-Hyun Kwon¹, Hyun-Min Seung¹, Kyoung-Cheol Kwon², Jong-Sun Lee¹, Myung-Jin Song¹, Han-Vit Jeoung¹, Young-Hye Son¹, and Jea-Gun Park^{1,2}
소속: ¹Department of Electronics and Computer Engineering, Hanyang University, ²Department of Nanoscale Semiconductor Engineering, Hanyang University
- WK3-K-5 16:50-17:05 Evolution of the Shape of the Conducting Channel in Complementary Resistive Switching Transition Metal Oxides**
저자: Kyung Jean Yoon, Seul Ji Song, Jun Yeong Seok, Jung Ho Yoon, Tae Hyung Park, Dae Eun Kwon, and Cheol Seong Hwang
소속: Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University